

Diode Chip

DSHP 20-18

supplies (UPS)

• ultrasonic cleaners & welders

Preliminary

Туре	V _{RRM}	I _{F(AV)}	Chi	p Size	Package		
	[V]	[A]	[mm]	x [mm]			
					sawn on foil	\checkmark	
DSHP 20-18	1800	23	4,45	4,45	unsawn wafer	∕*	
					in waffle pack	\checkmark	
					*Please Contact		
					IXYS Chip Sales		

Mechanical Parameters

Area active				8,62 mm²	Features	
Area total				19,80 mm²	 fast, soft SONIC diode 	
Wafer size Ø				150 mm	 low forward voltage drop 	
Thickness				290 μm	 small temp. Coefficient 	
Die Per Wafer				756		
Material				 low switching losses 		
Passivation front side				 high ruggedness 		
Metalisation front side			bondable:	Al	 anode top 	
Metalisation back side			solderable (only):	Al/Ti/NiV/Ag	• Tvjm = 175°C	
Recom. wire bonds (Al)		Anode	Number	3		
*= stitch bonds			Ø	380 μm	Applications	
Reject ink dot size		Ø		0.4 - 1.0 mm	 antiparallel diode for high 	
Recom. solder temp.				<300 °C	frequency switching	
Recom. Storage environment					 antisaturation diode 	
sawn on foil unsawn wafer		in org. co	ontainer, in dry nitrogen	<6 month	 snubber diode 	
		in org. co	ontainer, in dry nitrogen	<2 year	 freewheeling diode in 	
	in waffle pack in org. container, in		ontainer, in dry nitrogen	<2 year converters & motor c		
Storage temp.				-4040 °C	 rectifiers in switch mode 	
					power supplies (SMPS)	
					 inductive heating & melting 	
					 uninterruptible power 	

Dimensions

ABCD[mm][mm][mm]4,454,452,892,89		
Passivation	Anode (metal)	
	Cathode (metal)	
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N)	NW.SZJXC.C	



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Electrical Parameters

Symbol	Conditions		Ratings				
-				min	typ	max	Units
I _R	V = V _{RRM}	Tvj =	25 °C			50	μΑ
		Tvj =	150 °C		1		mA
V _F	If = 20 A	Tvj =	25 °C		1,90	2,20	V
		Tvj =	150 °C		2,00		V
V _{F0}	For power loss calculations onl	ly				1,4	V
r _F		Tvj =	175 °C			42,5	mΩ
Τ _ν				-55		175	°C
	DC	Tc =	80 °C		23		A
I _{FSM} *	V = OV	Tvj =	45 °C			150	A
R thJC *	DC current					1,7	K/W
Q _{rr}							μC
I _{RM}	V = 900 V	Tvj =	25 °C				А
t _{rr}	If = 20 A	dlf/dt =	500 A/µs				ns
E _{rec}							mJ
Q _{rr}					7		μC
I _{RM}	V = 900 V	Tvj =	150 °C		32		А
t _{rr}	lf = 20 A	dlf/dt =	500 A/µs		200		ns
E rec					3,5		mJ
	ding to assembled 280um DCP			Data and	rding to IEC	0747	F

* Data according to assembled 380 μ m DCB

Data according to IEC 60747

Terms of Conditions & Usage

The data contained in this product datasheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. Should you require product information in excess of the data given in this product datasheet or which concerns the specific application of our product, please contact the sales office, which is responsible for you. Due to technical requirements our product may contain dangerous substances. For any information on the types in question please contact the sales office/partner, which is responsible for you.

Should you intend to use the product in aviation applications, in life or health endangering or life support applications, please notify. For any such applications we urgently recommend

- to perform joint risks and quality assessments;

- the conclusion of quality agreements;

- to establish joint measures to ensure application specific product capabilities and notify that IXYS may deliver dependant on the realisation of any such measures.



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